

描述 / Descriptions

TO-220F 塑封封装 N 沟道 MOS 场效应管。N-CHANNEL MOSFET in a TO-220F Plastic Package.

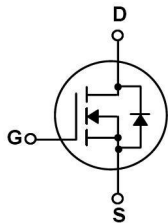
特征 / Features

低栅电荷,低反馈电容,开关速度快。
Low gate charge, low crss, fast switching.

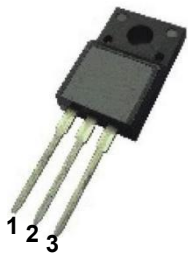
用途 / Applications

用于高功率 DC/DC 转换和功率开关。
These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

内部等效电路 / Equivalent Circuit



引脚排列 / Pinning



PIN1: G PIN 2: D PIN 3: S

放大及印章代码 / h_{FE} Classifications & Marking

见印章说明。 See Marking Instructions.

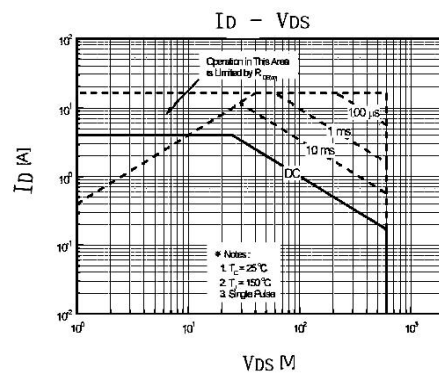
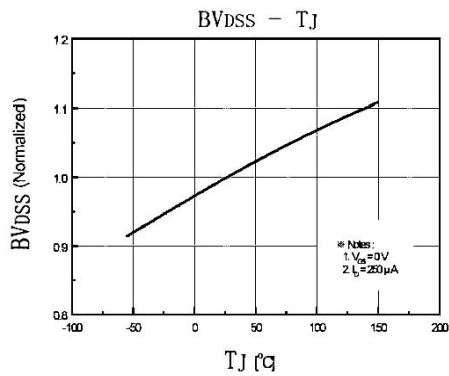
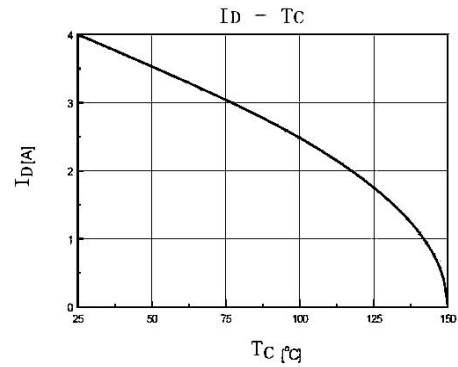
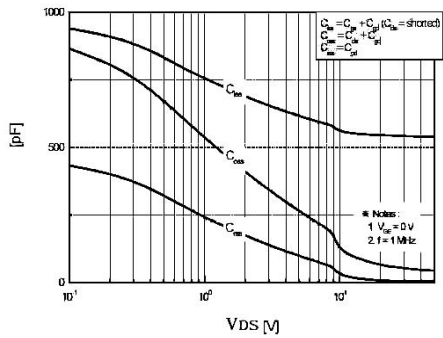
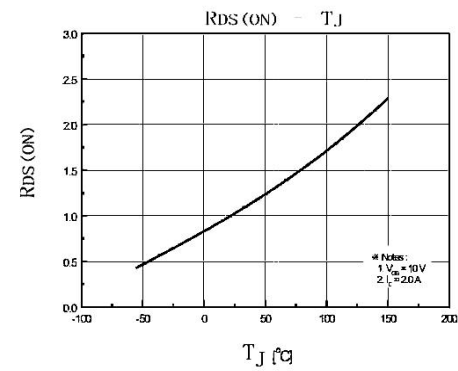
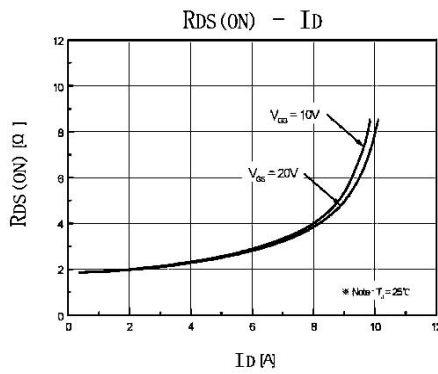
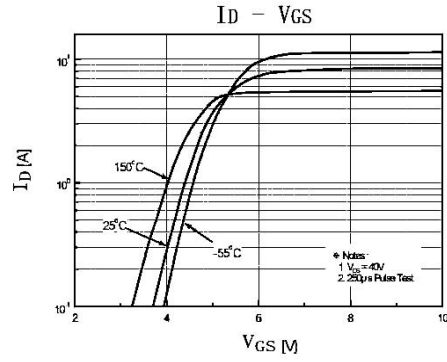
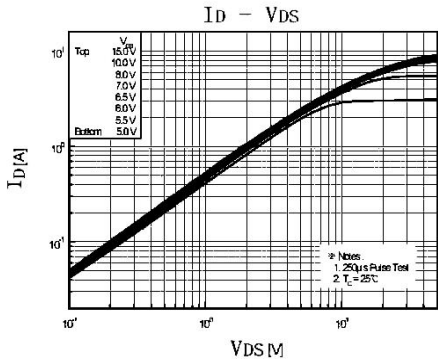
极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage	V_{DSS}	650	V
Drain Current	$I_D(T_C=25^\circ C)$	4.0	A
Drain Current	$I_D(T_C=100^\circ C)$	2.5	A
Drain Current - Pulsed	I_{DM}	16	A
Gate-Source Voltage	V_{GS}	±30	V
Single Pulsed Avalanche Energy	E_{AS}	240	mJ
Repetitive Avalanche Energy	E_{AR}	10	mJ
Avalanche Current	I_{AR}	4.0	A
Power Dissipation	$P_D(T_C=25^\circ C)$	33	W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C

电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250\mu A$	650			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=650V$ $V_{GS}=0V$			1	μA
		$V_{DS}=480V$ $T_C=125^\circ C$			100	μA
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=\pm 30V$ $V_{DS}=0V$			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	2.0		4.0	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=2.0A$			2.7	Ω
Forward Transconductance	g_{FS}	$V_{DS}=40V$ $I_D=2.0A$		4.7		S
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_S=4.0A$			1.4	V
Input Capacitance	C_{iss}	$V_{DS}=25V$ $V_{GS}=0V$ $f=1.0MHz$		545	710	pF
Output Capacitance	C_{oss}			60	80	
Reverse Transfer Capacitance	C_{rss}			8	11	
Reverse recovery time	t_{rr}	$I_{SD}=4.0A$ $di/dt=100A/\mu s$ $V_{DD}=24V$ $T_J = 150^\circ C$		400		ns
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=300V$ $I_D=4.0A$ $R_G=25\Omega$		10	30	ns
Turn-On Rise Time	t_r			35	80	
Turn-Off Delay Time	$t_{d(off)}$			45	100	
Turn-Off Fall Time	t_f			40	90	

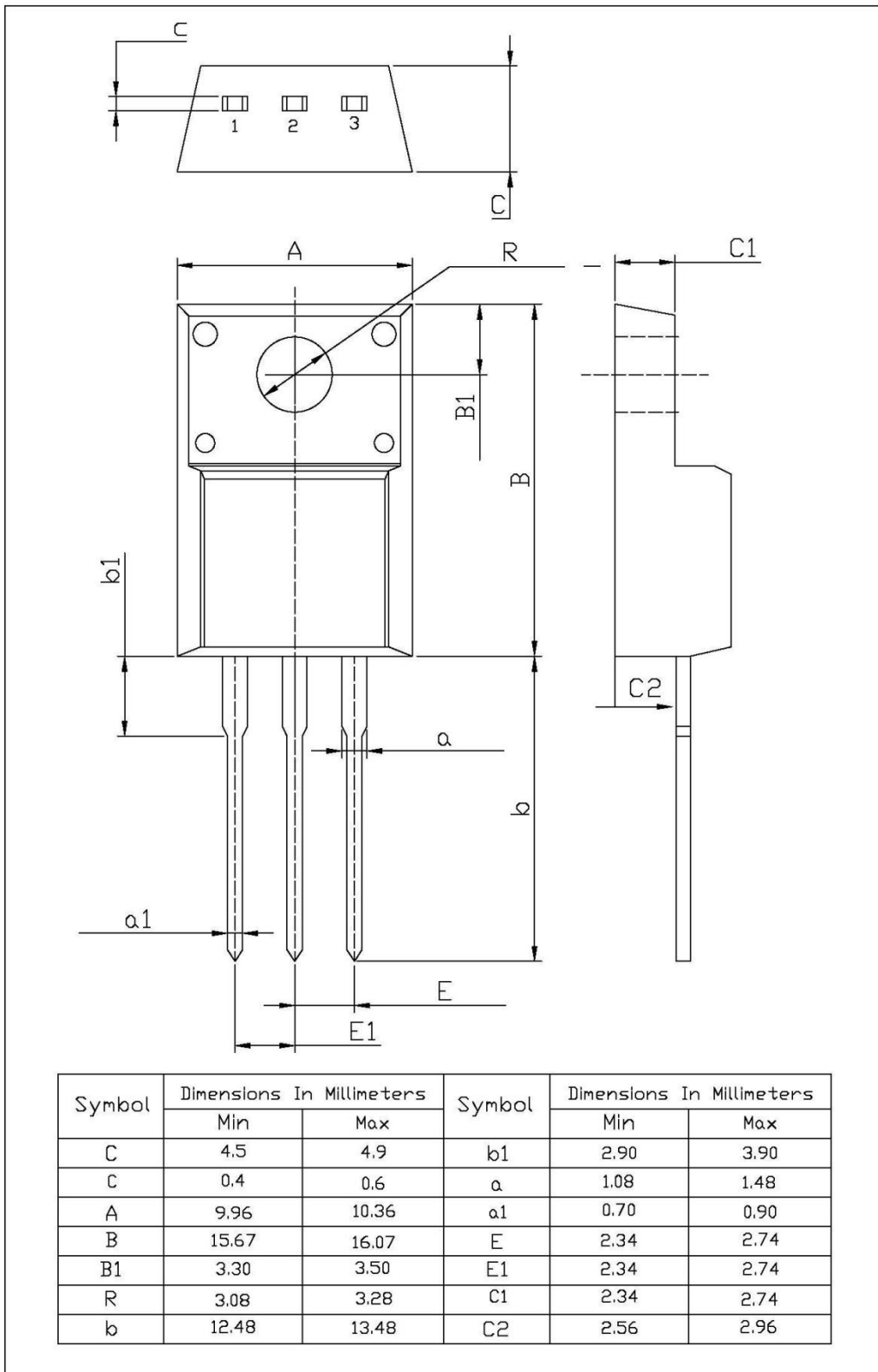
电参数曲线图 / Electrical Characteristic Curve



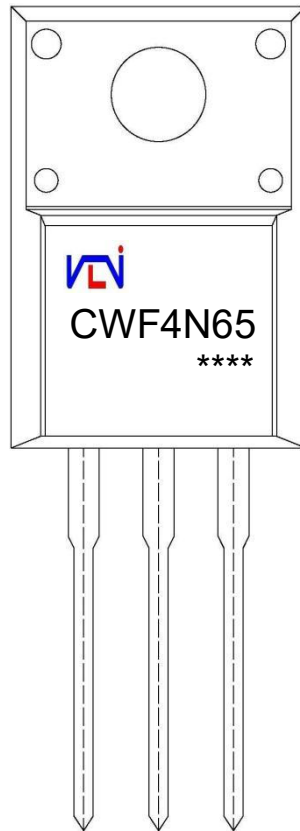
外形尺寸图 / Package Dimensions

TO-220FL

单位: mm



印章说明 / Marking Instructions



说明:

CWF: 为公司代码

4N65: 为型号代码

****: 为生产批号代码, 随生产批号变化。

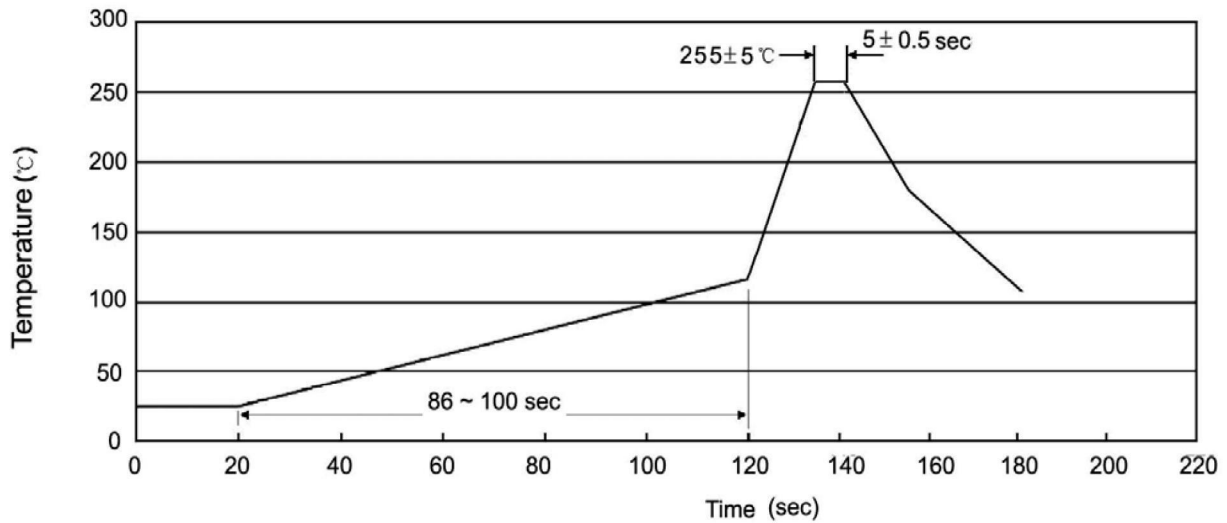
Note:

CWF: Company Code

4N65: Product Type.

****: Lot No. Code, code change with Lot No.

波峰焊温度曲线图(无铅) / Temperature Profile for Dip Soldering(Pb-Free)



说明:

- 1、预热温度 25 ~ 150°C, 时间 60 ~ 90sec;
- 2、峰值温度 255±5°C, 时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2 ~ 10°C/sec.

Note:

- 1.Preheating:25~150°C, Time:60~90sec.
- 2.Peak Temp.:255±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度: 270±5°C

时间: 10±1 sec.

Temp.:270±5°C

Time:10±1 sec

包装规格 / Packaging SPEC.

散件包装 / BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Bag 只/袋	Bags/Inner Box 袋/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Bag 袋	Inner Box 盒	Outer Box 箱
TO-220/F	200	10	2,000	5	10,000	135×190	237×172×102	560×245×195

套管包装 / TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱
TO-220/F	50	20	1,000	5	5,000	532×31.4×5.5	555×164×50	575×290×180

使用说明 / Notices